

**SANYO**

No.3508A

**2SK1467**

N-Channel MOS Silicon FET

Very High-Speed  
Switching Applications**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

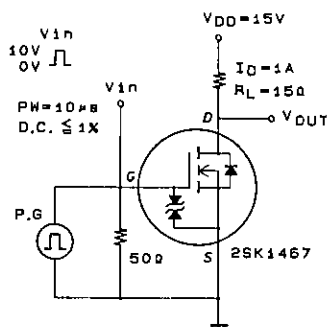
**Absolute Maximum Ratings at Ta = 25°C**

			unit	
Drain to Source Voltage	$V_{DS}$	30	V	
Gate to Source Voltage	$V_{GS}$	$\pm 15$	V	
Drain Current(DC)	$I_D$	2	A	
Drain Current(Pulse)	$I_{DP}$	8	A	
Allowable Power Dissipation	$P_D$	$T_c = 25^\circ\text{C}$	3.5	W
		Mounted on ceramic board (250mm <sup>2</sup> × 0.8mm)	1.5	W
Channel Temperature	$T_{ch}$	150	°C	
Storage Temperature	$T_{stg}$	- 55 to + 150	°C	

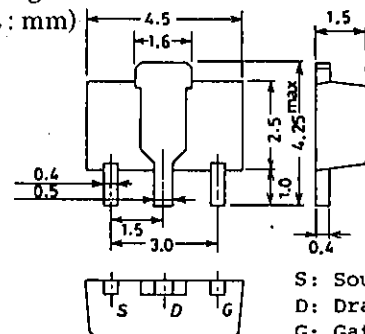
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0$	30			V
{ Zero Gate Voltage	$I_{DSS}$	$V_{DS} = 30\text{V}, V_{GS} = 0$			100	$\mu\text{A}$
{ Drain Current						
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12\text{V}, V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}, I_D = 1\text{mA}$	1.0		2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}, I_D = 1\text{A}$	1.2	2.0		S
{ Static Drain to Source	$R_{DS(on)}$	$I_D = 1\text{A}, V_{GS} = 10\text{V}$		0.2	0.3	$\Omega$
			{ on State Resistance	$I_D = 1\text{A}, V_{GS} = 4\text{V}$	0.3	0.45
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		170		pF
Output Capacitance	$C_{oss}$	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		100		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = 10\text{V}, f = 1\text{MHz}$		30		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7		ns
Rise Time	$t_r$	"		11		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		35		ns
Fall Time	$t_f$	"		25		ns
Diode Forward Voltage	$V_{SD}$	$I_S = 2\text{A}, V_{GS} = 0$		1.0		V

Marking: KC

**Switching Time Test Circuit****Package Dimensions 2062**

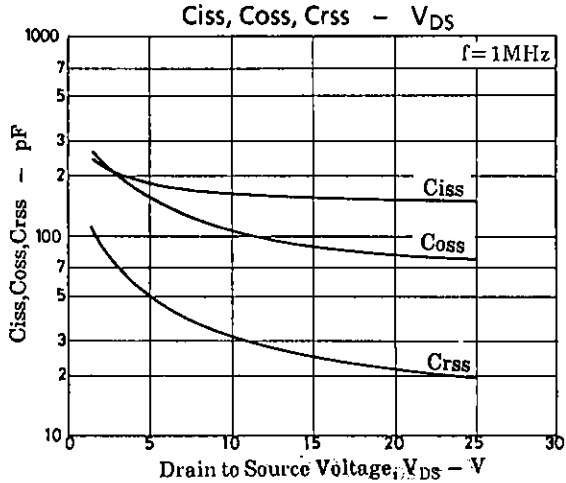
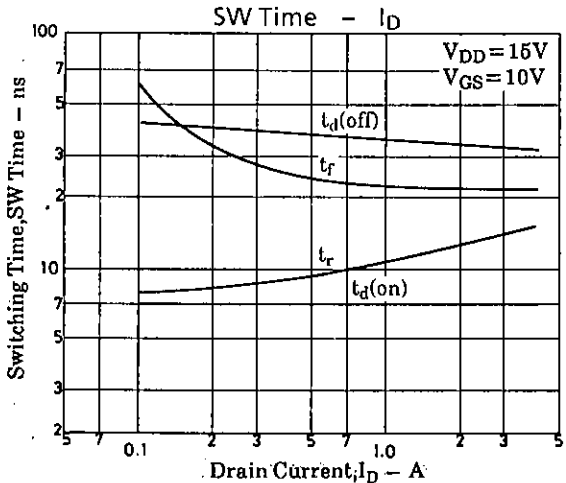
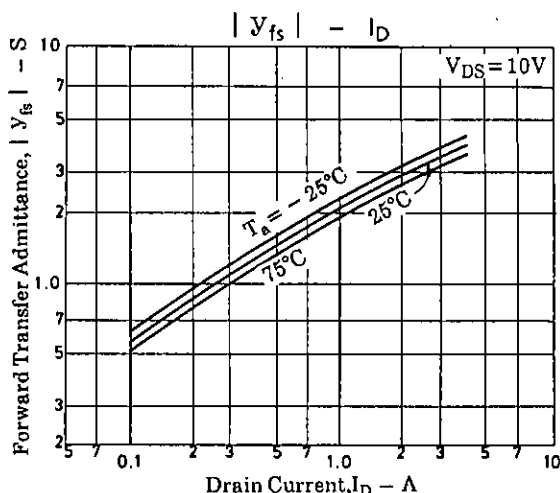
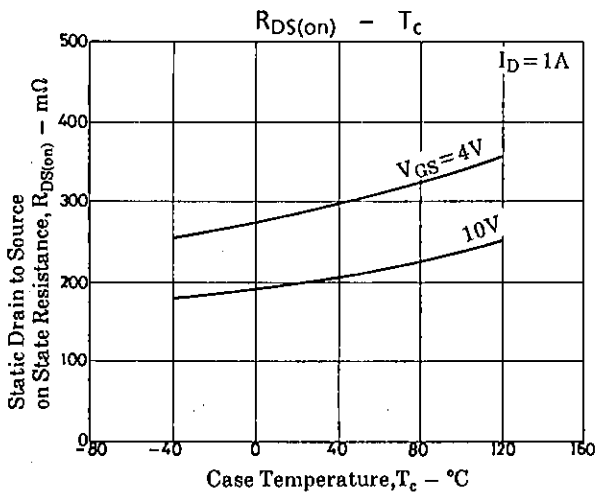
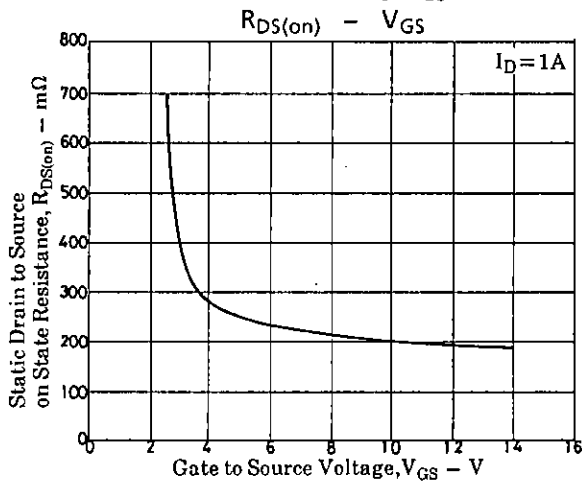
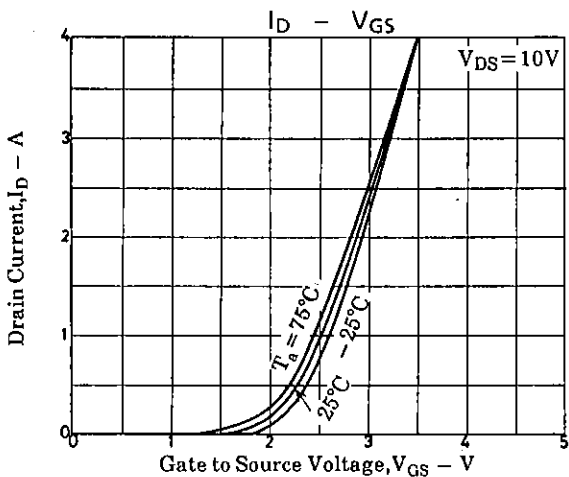
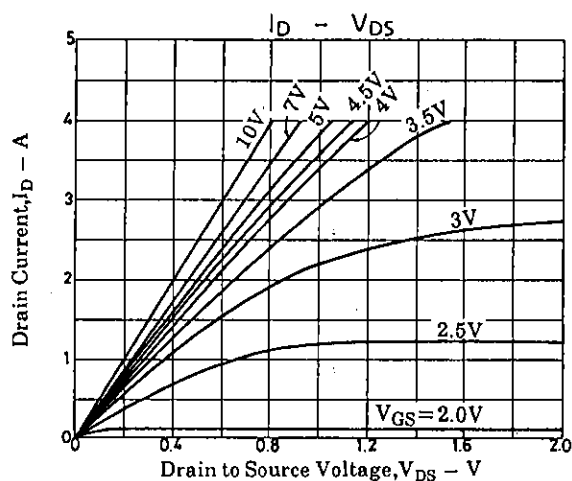
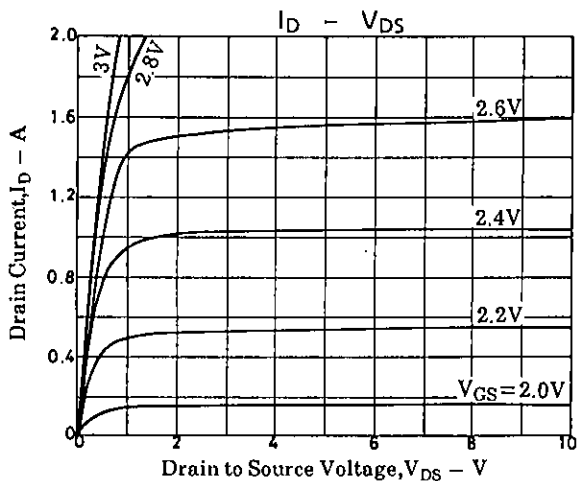
(unit: mm)

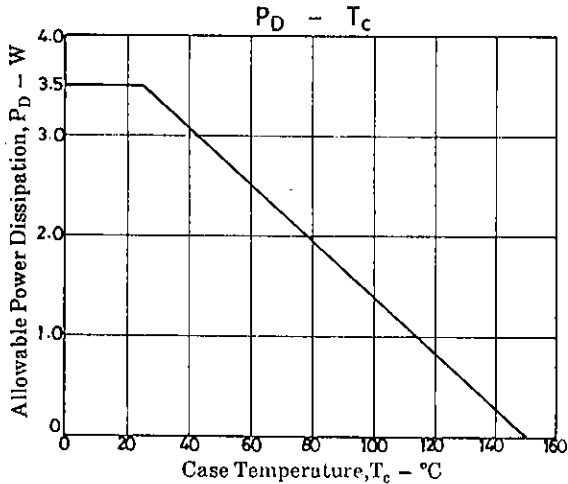
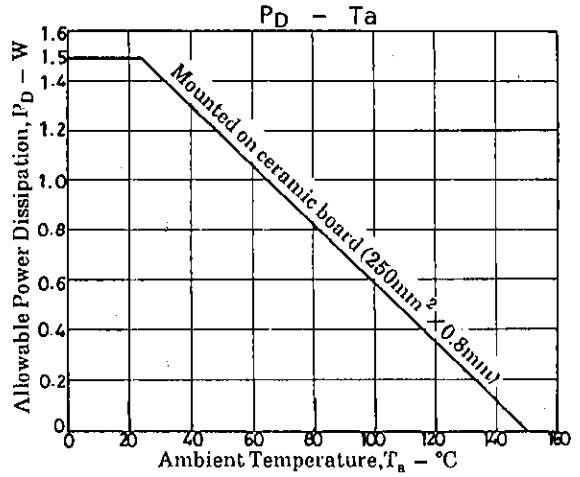
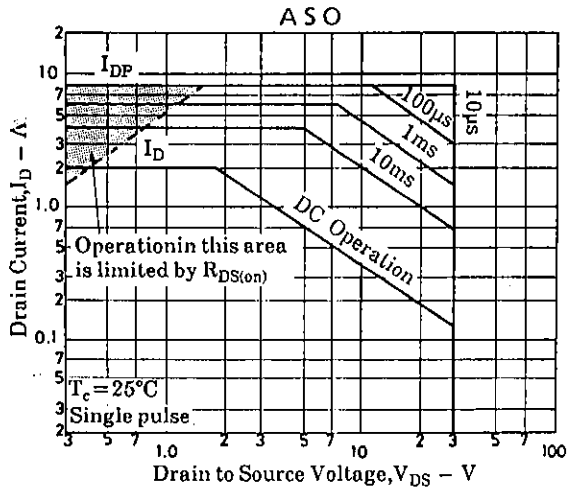
S: Source  
D: Drain  
G: Gate

SANYO: PCP

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